PJB772/PJB772S
PNP Epitaxial Silicon Transistor

AUDIO FREQUENCY POWER AMPLIFIER
LOW SPEED SWITCHING

- Complement to PJD882
- PW 10μs,Duty Cycle 50%
- Pulse Test PW 350μs,Duty Cycle 2%

TO-92 TO-126



Pin : 1.Emitter
2.Collector
3.Base

ABSOLUTE MAXIMUM RATINGS (Ta = 25℃)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Bias Voltage	V_{EBO}	-5	V
Collector Current (DC)	I_C	-2	A
*Collector Current (Pulse)	I_C	-5	A
Base Current (DC)	I_B	-0.6	A
Collector Dissipation (Ta=25℃)	P_C	-	W
Collector Dissipation (Tc=25℃)	P_C	1	W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55~150	℃

ORDERING INFORMATION

Device	Operating Temperature	Package
PJB772SCT	-20℃～+85℃	TO-92
PJB772CK		TO-126

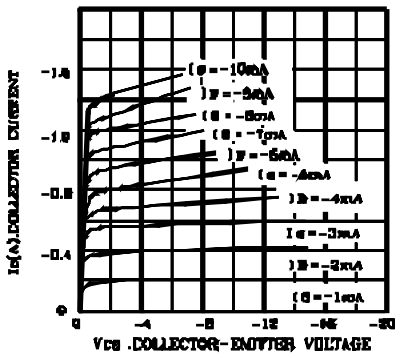
ELECTRICAL CHARACTERISTICS (Ta = 25℃)

Characteristics	Symbol	Test condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB}=-30V,I_E=0			-1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=-3V,I_C=0			-1	μA
*DC Current Gain	h_{FE1}	V_{CE}=-2V,I_C=-20mA	30	220		
	h_{FE2}	V_{CE}=-2V,I_C=-1A	60	160	400	
*Collector Emitter Saturation	$V_{CE(SAT)}$	I_C=-2A,I_B=-0.2A		-0.3	-0.45	V
Voltage	$V_{BE(SAT)}$	I_C=-2A,I_B=-0.2A		-1.0	-2.0	V
*Base Emitter Saturation Voltage	f_T	V_{CE}=-5V,I_C=0.1A		80		MHz
Current Gain Bandwidth Product	Cob	V_{CB}=-10V,I_E=0		55		pF
Output Capacitance		f=1MHz				
	NF	V_{CE}=10V,I_C=1mA		4		dB
Noise Figure		R_S=10K ,f=1KHz				

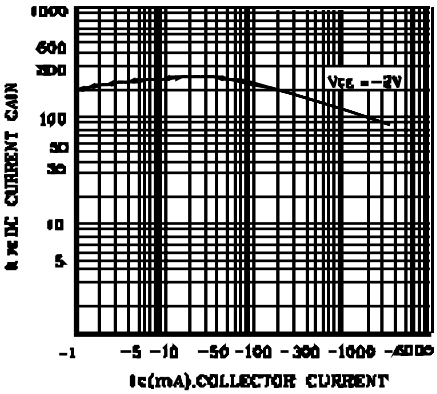
h_{FE}(2) CLASSIFICATION

Classification	R	O	Y	G
h_{FE}(2)	60-120	100-200	160-320	200-400

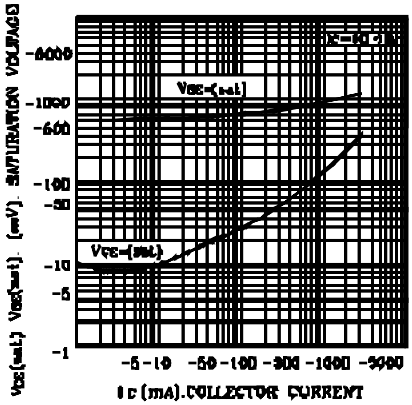
STATIC CHARACTERISTIC



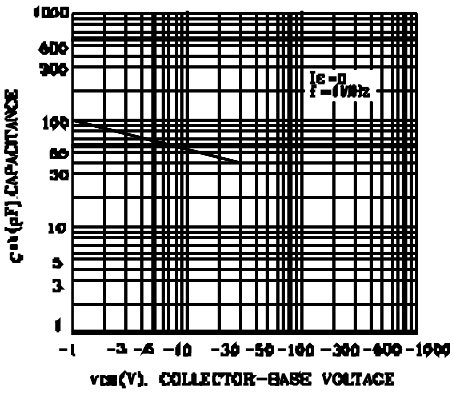
DC CURRENT GAIN



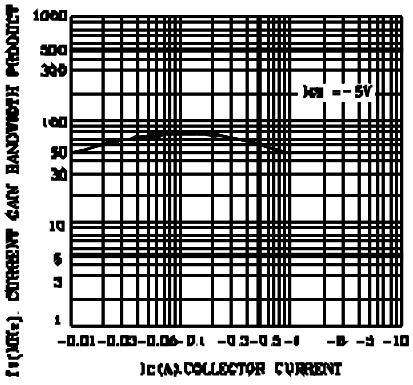
BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



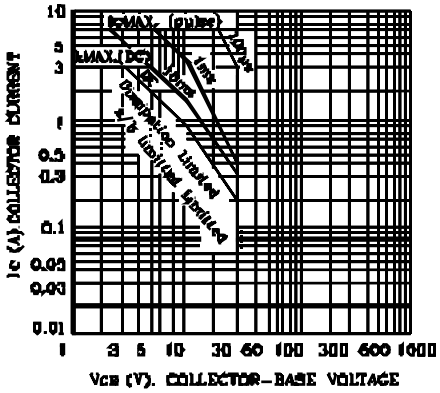
COLLECTOR OUTPUT CAPACITANCE



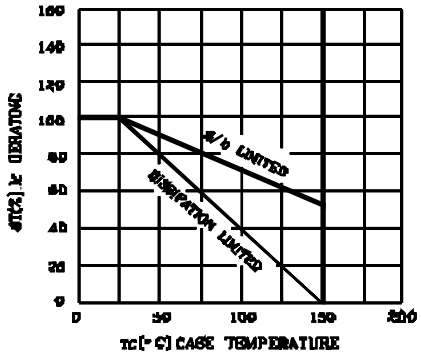
CURRENT GAIN-BANDWIDTH PRODUCT



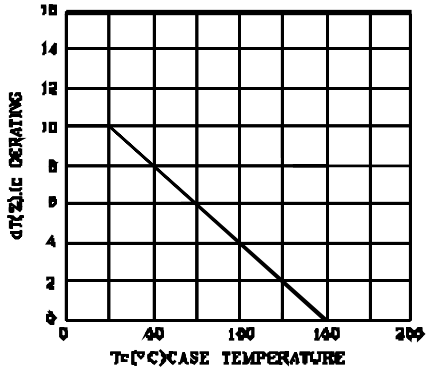
SAFE OPERATING AREAS



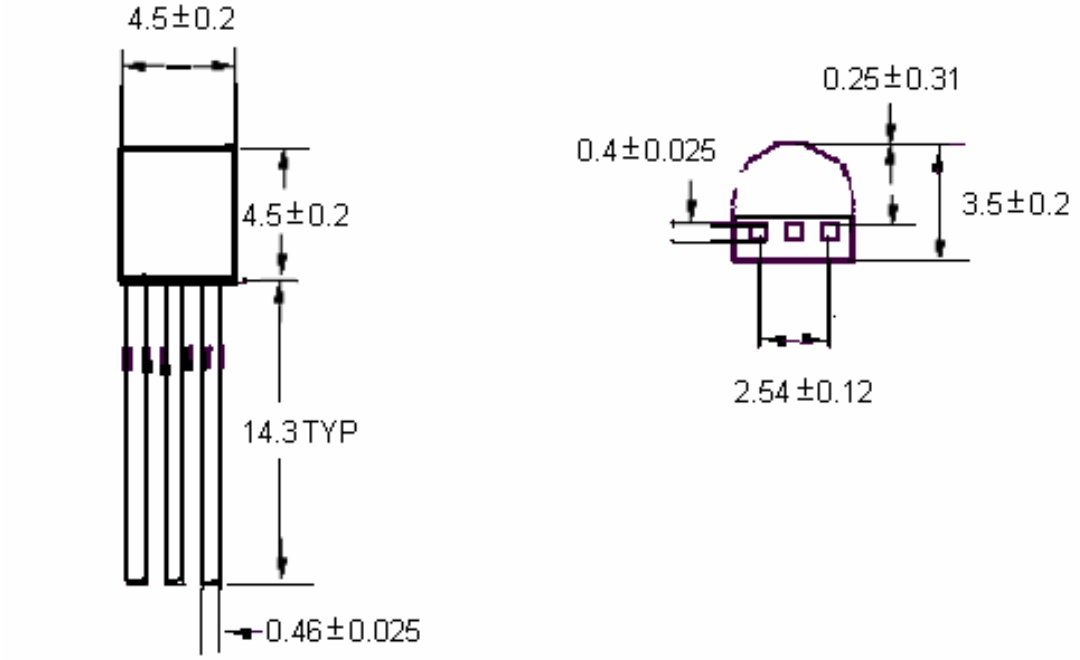
DERATING CURVE OF SAFE OPERATING AREAS



POWER DERATING



TO-92 Unit:mm



TO-126 Unit:mm

